Tentative Program as of May 19:

10:00-10:10 **Opening remark: Chair: K. Ohuchi**
from T. Kimoto, B. Zhao

Session 1: Keynote and Junction Technology Review 1: Chair: S. Shishiguchi

10:10-10:40 **H. Iwai,** "The Centennial of FET and the Silver Jubilee of IWJT: Tracing the Origins and Evolution of Junction Technology in FETs

10:40-11:00 **B. Mizuno**, "Plasma doping & Technology Overview or Did Shallow Junction demand a competitive evolution to Super Low-energy implantation, Plasma Doping, Solid Phase Diffusion and Epi-doping? + a Review of Plasma Doping appeared in past IWJT"

11:00-11:25 **J. Borland**, "Gas/Vapor Phase Epi (VPE), Liquid Phase Epi (LPE) & Solid Phase Epi (SPE) Doping Methods in Si, SiGe and Ge: A Historical Review"

11:25-11:50 **M. Current and Y. Kawasaki**, "Ion Channeling in Si and SiC: A historical review"

11:50-11:55 **Photo Session**

11:55-12:45 **Lunch**

Session 2: Junction Technology Review 2: Chair: B. Mizuno

12:45-13:10 **K. Tsutsui, T. Matsushita and Y. Morikawa**,
"Observation of Three-dimensional Atomic Arrangements Corresponding to Electrical Activation/Deactivation of As doped in Si"

13:10-13:35 **M. Tanjo**, "Implantation Technologies and equipment"

13:35-14:00 **J. Matsuo**, "Cluster Implantation"

14:00-14:25 **O. Nakatsuka**, "Silicide Technology for Metal/Semiconductor Contact on ULSI and Nanoelectronics Applications"

14:25-14:50 **H. Wakabayashi**, "Device technology"

14:50-15:10 **Break**

15:10-17:10 **Panel Discussion:**
"25 Years of IWJT History, FET100 and Future Directions in Junction Technology"
Organizers: **M. Tanjo, B. Mizuno, S. Shishiguchi, H.Iwai**
Moderators: **H. Ito and I. Mizushima**
Panelist: **Short-presenters +M. Current, J. Borland, J. Matsuo, H. Iwai etc.**
Short presentations: 11 people x 3 min = 33 min
Panel discussions: 1 hour 27 min

17:10-17:15 **Closing remark: Chair: M. Tanjo**
from S. Shibata